μ**PA2660T1**R

DUAL N-CHANNEL MOSFET

20 V, 4.0 A, 42 m $\Omega$ 

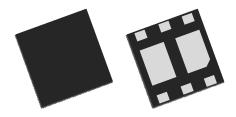
## Description

The  $\mu$ PA2660T1R is Dual N-channel MOS Field Effect Transistors for switching application.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

## Features

- DS MAXIMUM RATINGS  $20V(T_A = 25^{\circ}C)$
- 2.5V drive available
- Low on-state resistance
  - ----  $R_{DS \mbox{ (on)}1}$  = 42 m $\Omega$  MAX. (V\_{GS} = 4.5 V, I\_D = 2.0 A)
  - ----  $R_{DS (on)2} = 62 \text{ m}\Omega \text{ MAX.} (V_{GS} = 2.5 \text{ V}, I_D = 2.0 \text{ A})$
- Built-in gate protection diode
- Lead-free and Halogen-free



6pinHUSON2020(Dual)

## **Ordering Information**

Part Number	Package		
μPA2660T1R-E2-AX* <sup>1</sup>	6pinHUSON2020(Dual)		

Note: \*1.Pb-free (This product does not contain Pb in the external electrode and other parts.)

# Absolute Maximum Ratings (T<sub>A</sub> = 25°C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage ( $V_{GS}$ = 0 V)	V <sub>DSS</sub>	20	V
Gate to Source Voltage ( $V_{DS} = 0 V$ )	V <sub>GSS</sub>	±12	V
Drain Current (DC)	I <sub>D(DC)</sub>	±4.0	А
Drain Current (pulse) *1	I <sub>D(pulse)</sub>	±16	А
Total Power Dissipation (1 unit, 5 s) *2	P <sub>T1</sub>	1.5	W
Total Power Dissipation (2 units, 5 s) *2	P <sub>T2</sub>	2.3	W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C

Notes: \*1. PW≤10  $\mu$ s, Duty Cycle≤1%

\*2. Mounted on glass epoxy board of 25.4mm x 25.4mm x 0.8mmt

Caution: This product is electrostatic-sensitive device due to low ESD capability and should be handled with caution for electrostatic discharge.

 $V_{ESD}$  = ±400V MIN. ( C = 100pF, R = 1.5K $\Omega$  )

R07DS0999EJ0100

Rev.1.00

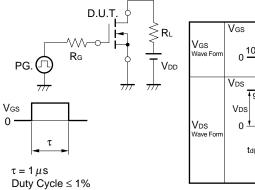
Jan 16, 2013

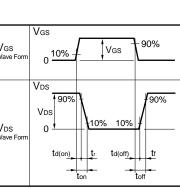
# **Electrical Characteristics (T<sub>A</sub> = 25°C)**

Characteristics	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			1.0	μA	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V	
Gate Leakage Current	I <sub>GSS</sub>			±10	μA	$V_{GS}$ = ±10 V, $V_{DS}$ = 0 V	
Gate Cut-off Voltage	V <sub>GS(off)</sub>	0.5		1.5	V	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	
Forward Transfer Admittance *1	y <sub>fs</sub>	5.0			S	$V_{DS}$ = 10 V, $I_{D}$ = 2.0 A	
Drain to Source On-state	R <sub>DS(on)1</sub>		33	42	mΩ	$V_{GS}$ = 4.5 V, I <sub>D</sub> = 2.0 A	
Resistance *1	R <sub>DS(on)2</sub>		43	62	mΩ	$V_{GS}$ = 2.5 V, I <sub>D</sub> = 2.0 A	
Input Capacitance	C <sub>iss</sub>		330		pF	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz	
Output Capacitance	C <sub>oss</sub>		66		pF		
Reverse Transfer Capacitance	C <sub>rss</sub>		38		pF		
Turn-on Delay Time	t <sub>d (on)</sub>		12		ns	I <sub>D</sub> = 2.0 A, V <sub>DD</sub> = 10 V,	
Rise Time	t <sub>r</sub>		6.4		ns	$V_{GS}$ = 4.5 V, $R_{G}$ = 6 $\Omega$	
Turn-off Delay Time	t <sub>d (off)</sub>		27		ns		
Fall Time	t <sub>f</sub>		6.6		ns		
Total Gate Charge	Q <sub>G</sub>		4.5		nC	I <sub>D</sub> = 4.0 A , V <sub>DD</sub> = 16 V, V <sub>GS</sub> = 10 V	
Gate to Source Charge	Q <sub>GS</sub>		1.0		nC		
Gate to Drain Charge	Q <sub>GD</sub>		1.5		nC		
Body Diode Forward Voltage *1	V <sub>F(S-D)</sub>			1.5	V	I <sub>F</sub> = 4.0 A, V <sub>GS</sub> = 0 V	

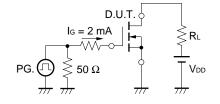
Note: \*1. Pulsed

## **TEST CIRCUIT 1 SWITCHING TIME**





## **TEST CIRCUIT 2 GATE CHARGE**

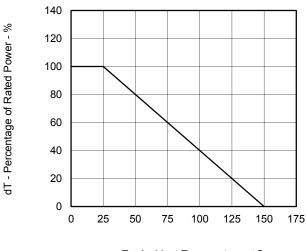




I<sub>D</sub> – Drain Current - A

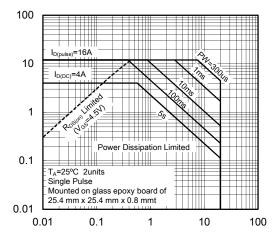
# Typical Characteristics $(T_A = 25^{\circ}C)$

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

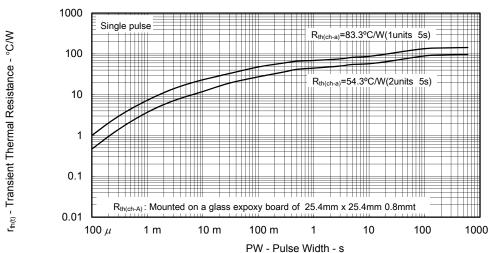


T<sub>A</sub> -Ambient Temperature - °C





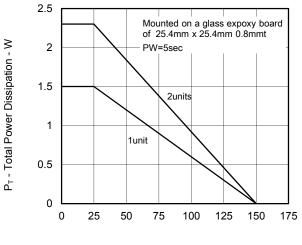




TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

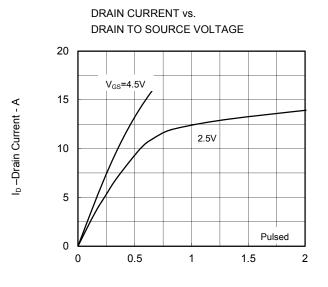
AMBIENT TEMPERATURE

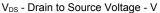
TOTAL POWER DISSIPATION vs.

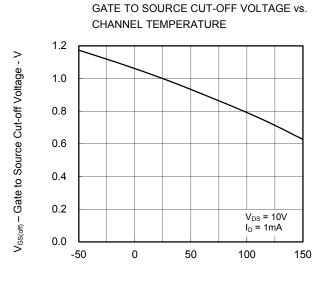


T<sub>A</sub> -Ambient Temperature - °C

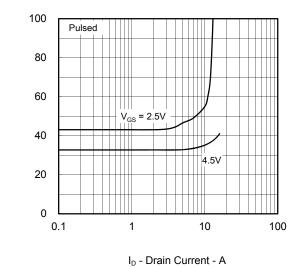






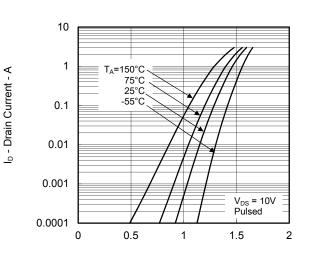


T<sub>ch</sub> - Channel Temperature - °C

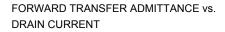


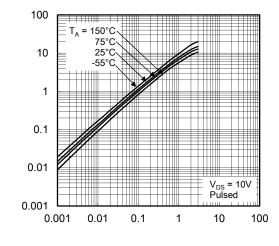
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

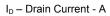
FORWARD TRANSFER CHARACTERISTICS

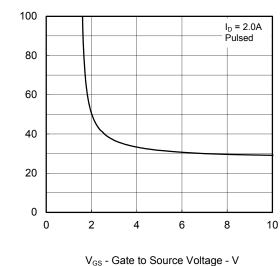


V<sub>GS</sub> - Gate to Source Voltage - V









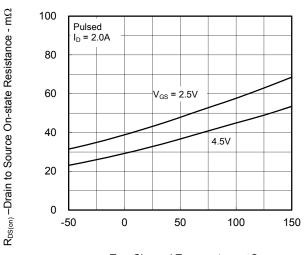
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

# $R_{\text{DS}(\text{on})}$ - Drain to Source On-state Resistance - $m\Omega$



| y<sub>fs</sub> | - Forward Transfer Admittance - S

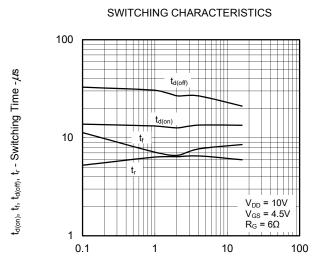
 $R_{\text{DS(on)}}$  – Drain to Source On-state Resistance -  $m\Omega$ 

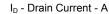


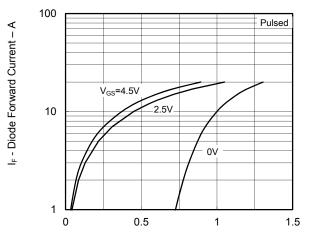
DRAIN TO SOURCE ON-STATE RESISTANCE vs.

CHANNEL TEMPERATURE

T<sub>ch</sub> - Channel Temperature - °C



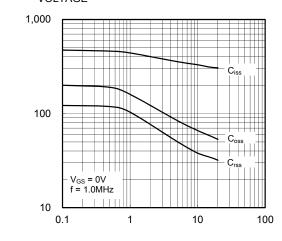




SOURCE TO DRAIN DIODE FORWARD VOLTAGE

 $V_{F(S\!-\!D)}$  - Drain to Source Voltage - V

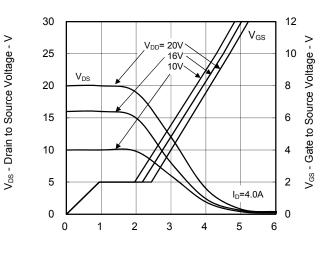
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



Ciss, Coss, Crss - Capacitance - pF

V<sub>DS</sub> – Drain to Source Voltage - V

DYNAMIC INPUT/OUTPUT CHARACTERISTICS

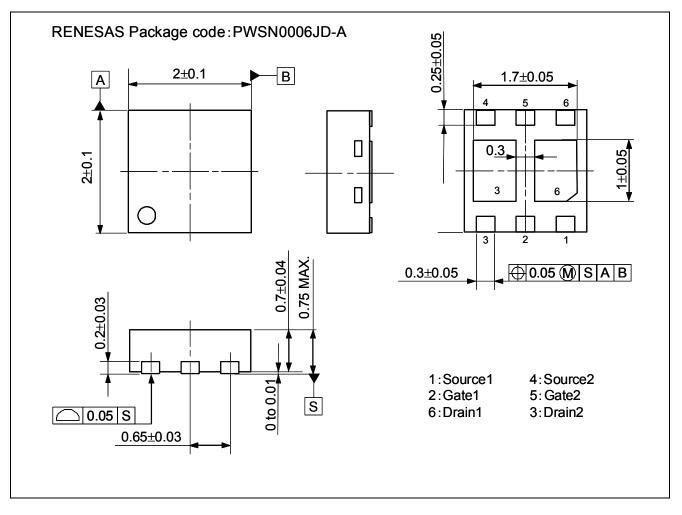


Q<sub>G</sub> - Gate Charge - nC

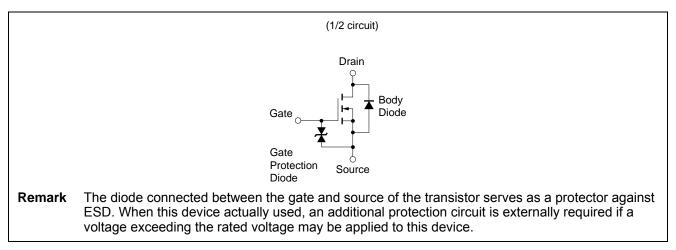


# Package Drawings (Unit: mm)

## 6pinHUSON2020



# **Equivalent Circuit**





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